

74HC3G07-Q100; 74HCT3G07-Q100

Triple buffer with open-drain outputs

Rev. 2 — 11 December 2013

Product data sheet

1. General description

The 74HC3G07-Q100; 74HCT3G07-Q100 is a triple buffer with open-drain outputs. Inputs include clamp diodes that enable the use of current limiting resistors to interface inputs to voltages in excess of V_{CC} .

This product has been qualified to the Automotive Electronics Council (AEC) standard Q100 (Grade 1) and is suitable for use in automotive applications.

2. Features and benefits

- Automotive product qualification in accordance with AEC-Q100 (Grade 1)
 - ◆ Specified from $-40\text{ }^{\circ}\text{C}$ to $+85\text{ }^{\circ}\text{C}$ and from $-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$
- Input levels:
 - ◆ For 74HC3G07-Q100: CMOS level
 - ◆ For 74HCT3G07-Q100: TTL level
- Complies with JEDEC standard no. 7 A
- Wide supply voltage range from 2.0 V to 6.0 V
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- ESD protection:
 - ◆ MIL-STD-883, method 3015 exceeds 2000 V
 - ◆ HBM JESD22-A114F exceeds 2000 V
 - ◆ MM JESD22-A115-A exceeds 200 V ($C = 200\text{ pF}$, $R = 0\text{ }\Omega$)
- Multiple package options

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC3G07DP-Q100 74HCT3G07DP-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC3G07DC-Q100 74HCT3G07DC-Q100	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1



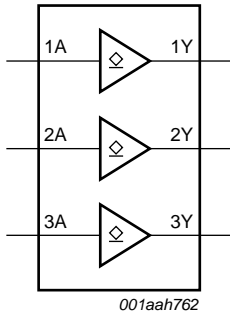
4. Marking

Table 2. Marking code

Type number	Marking code ^[1]
74HC3G07DP-Q100	H07
74HCT3G07DP-Q100	T07
74HC3G07DC-Q100	H07
74HCT3G07DC-Q100	T07

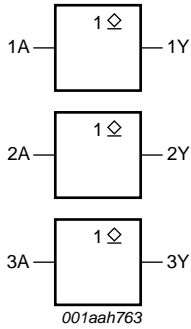
[1] The pin 1 indicator is located on the lower left corner of the device, below the marking code.

5. Functional diagram



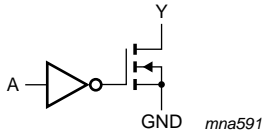
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Fig 1. Logic symbol



001aah763

Fig 2. IEC logic symbol



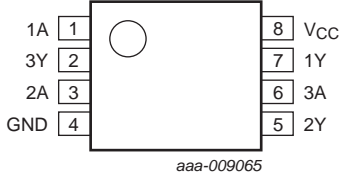
mna591

Fig 3. Logic diagram (one buffer)

6. Pinning information

6.1 Pinning

74HC3G07-Q100
74HCT3G07-Q100



aaa-009065

Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

6.2 Pin description

Table 3. Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V _{CC}	8	supply voltage

7. Functional description

Table 4. Function table^[1]

Input nA	Output nY
L	L
H	Z

[1] H = HIGH voltage level; L = LOW voltage level; Z = high-impedance OFF-state.

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{CC}	supply voltage		-0.5	7.0	V
I _{IK}	input clamping current	V _I < -0.5 V or V _I > V _{CC} + 0.5 V	^[1] -	±20	mA
I _{OK}	output clamping current	V _O < -0.5 V	^[1] -20	-	mA
V _O	output voltage	active mode	^[1] -0.5	V _{CC} + 0.5	V
		high-impedance mode	^[1] -0.5	7.0	V
I _O	output current	V _O = -0.5 V to 7.0 V	^[1] -25	-	mA
I _{CC}	supply current		^[1] -	50	mA
I _{GND}	ground current		^[1] -50	-	mA
T _{stg}	storage temperature		-65	+150	°C
P _D	dynamic power dissipation	T _{amb} = -40 °C to +125 °C	^[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P_{tot} derates linearly with 2.5 mW/K.
For VSSOP8 package: above 110 °C the value of P_{tot} derates linearly with 8 mW/K.

9. Recommended operating conditions

Table 6. Recommended operating conditions

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC3G07-Q100			74HCT3G07-Q100			Unit
			Min	Typ	Max	Min	Typ	Max	
V _{CC}	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V _I	input voltage		0	-	6.0	0	-	5.5	V
V _O	output voltage		0	-	V _{CC}	0	-	V _{CC}	V
T _{amb}	ambient temperature		-40	+25	+125	-40	+25	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V _{CC} = 2.0 V	-	-	625	-	-	-	ns/V
		V _{CC} = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V _{CC} = 6.0 V	-	-	83	-	-	-	ns/V

10. Static characteristics

Table 7. Static characteristics

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T_{amb} = 25 °C.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
74HC3G07-Q100								
V _{IH}	HIGH-level input voltage	V _{CC} = 2.0 V	1.5	1.2	-	1.5	-	V
		V _{CC} = 4.5 V	3.15	2.4	-	3.15	-	V
		V _{CC} = 6.0 V	4.2	3.2	-	4.2	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 2.0 V	-	0.8	0.5	-	0.5	V
		V _{CC} = 4.5 V	-	2.1	1.35	-	1.35	V
		V _{CC} = 6.0 V	-	2.8	1.8	-	1.8	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 20 μA; V _{CC} = 2.0 V	-	0	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I _O = 20 μA; V _{CC} = 6.0 V	-	0	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
		I _O = 5.2 mA; V _{CC} = 6.0 V	-	0.16	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 6.0 V	-	-	±0.1	-	±1.0	μA
I _{LO}	output leakage current	V _I = V _{IH} ; V _O = V _{CC} or GND	-	-	±5.0	-	±10	μA
I _{CC}	supply current	per input pin; V _{CC} = 6.0 V; V _I = V _{CC} or GND; I _O = 0 A;	-	-	10	-	20	μA
C _I	input capacitance		-	1.5	-	-	-	pF

Table 7. Static characteristics ...continued

Voltages are referenced to GND (ground = 0 V). All typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ ^[1]	Max	Min	Max	
74HCT3G07-Q100								
V _{IH}	HIGH-level input voltage	V _{CC} = 4.5 V to 5.5 V	2.0	1.6	-	2.0	-	V
V _{IL}	LOW-level input voltage	V _{CC} = 4.5 V to 5.5 V	-	1.2	0.8	-	0.8	V
V _{OL}	LOW-level output voltage	V _I = V _{IH} or V _{IL}						
		I _O = 20 μA; V _{CC} = 4.5 V	-	0	0.1	-	0.1	V
		I _O = 4.0 mA; V _{CC} = 4.5 V	-	0.15	0.33	-	0.4	V
I _I	input leakage current	V _I = V _{CC} or GND; V _{CC} = 5.5 V	-	-	±1.0	-	±1.0	μA
I _{LO}	output leakage current	V _I = V _{IH} ; V _O = V _{CC} or GND	-	-	±5.0	-	±10	μA
I _{CC}	supply current	per input pin; V _{CC} = 5.5 V; V _I = V _{CC} or GND; I _O = 0 A;	-	-	10	-	20	μA
ΔI _{CC}	additional supply current	per input; V _{CC} = 4.5 V to 5.5 V; V _I = V _{CC} − 2.1 V; I _O = 0 A	-	-	375	-	410	μA
C _I	input capacitance		-	1.5	-	-	-	pF

[1] Typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$.

11. Dynamic characteristics

Table 8. Dynamic characteristics

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$; for test circuit, see [Figure 6](#).

Symbol	Parameter	Conditions	−40 °C to +85 °C			−40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HC3G07-Q100								
t _{PZL}	OFF-state to LOW propagation delay	nA to nY; see Figure 5						
		V _{CC} = 2.0 V	-	25	95	-	125	ns
		V _{CC} = 4.5 V	-	9	19	-	25	ns
		V _{CC} = 6.0 V	-	7	16	-	20	ns
t _{PLZ}	LOW to OFF-state propagation delay	nA to nY; see Figure 5						
		V _{CC} = 2.0 V	-	25	95	-	125	ns
		V _{CC} = 4.5 V	-	11	23	-	30	ns
		V _{CC} = 6.0 V	-	10	23	-	26	ns
t _{THL}	HIGH to LOW output transition time	nY; see Figure 5						
		V _{CC} = 2.0 V	-	18	95	-	125	ns
		V _{CC} = 4.5 V	-	6	19	-	25	ns
		V _{CC} = 6.0 V	-	5	16	-	20	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC}	[1]	-	4	-	-	pF

Table 8. Dynamic characteristics ...continued

Voltages are referenced to GND (ground = 0 V); all typical values are measured at $T_{amb} = 25\text{ }^{\circ}\text{C}$; for test circuit, see [Figure 6](#).

Symbol	Parameter	Conditions	–40 °C to +85 °C			–40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	
74HCT3G07-Q100								
t _{PZL}	OFF-state to LOW propagation delay	nA to nY; see Figure 5 V _{CC} = 4.5 V	-	11	27	-	32	ns
t _{PLZ}	LOW to OFF-state propagation delay	nA to nY; see Figure 5 V _{CC} = 4.5 V	-	10	26	-	31	ns
t _{THL}	HIGH to LOW output transition time	V _{CC} = 4.5 V; see Figure 5	-	6	19	-	22	ns
C _{PD}	power dissipation capacitance	V _I = GND to V _{CC} – 1.5 V [1]	-	4		-	-	pF

[1] C_{PD} is used to determine the dynamic power dissipation (P_D in μW).

$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o)$ where:

f_i = input frequency in MHz;

f_o = output frequency in MHz;

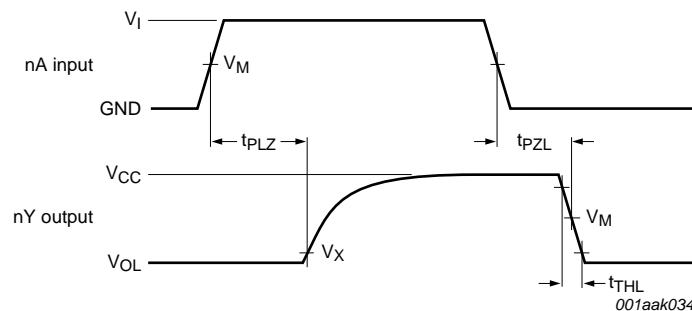
C_L = output load capacitance in pF;

V_{CC} = supply voltage in V;

N = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$ = sum of outputs.

12. Waveforms



Measurement points are given in [Table 9](#).

V_{OL} is the typical output voltage level that occurs with the output load.

Fig 5. The input (nA) to output (nY) propagation delays

Table 9. Measurement points

Type	Input	Output	
	V_M	V_M	V_X
74HC3G07-Q100	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$	$0.1 \times V_{CC}$
74HCT3G07-Q100	1.3 V	1.3 V	$0.1 \times V_{CC}$

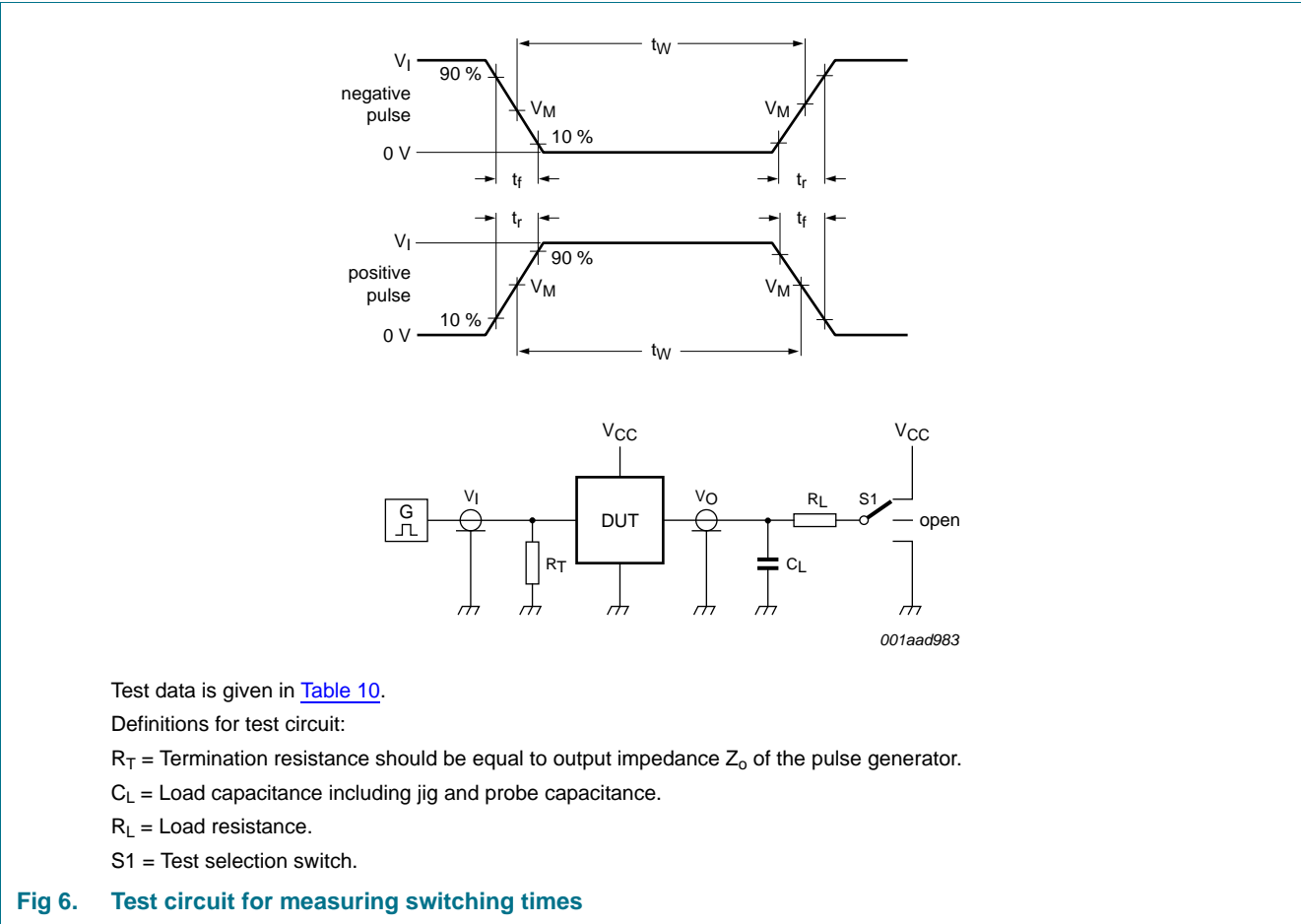


Table 10. Test data

Type	Input		Load		S1 position
	V _I	t _r , t _f	C _L	R _L	t _{pZL} , t _{pLZ}
74HC3G07-Q100	GND to V _{CC}	≤ 6 ns	50 pF	1 kΩ	V _{CC}
74HCT3G07-Q100	GND to 3 V	≤ 6 ns	50 pF	1 kΩ	V _{CC}

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

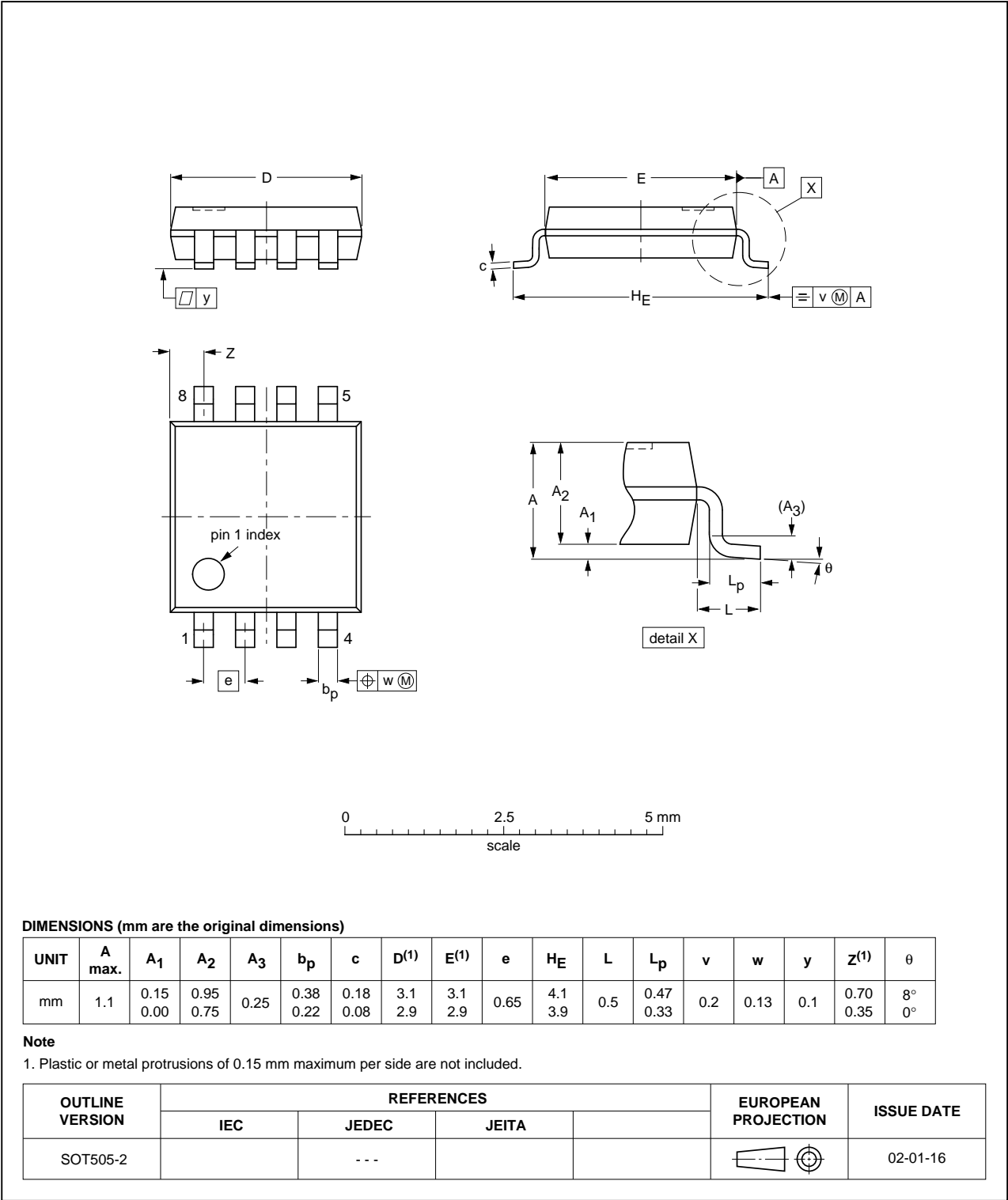


Fig 7. Package outline SOT505-2 (TSSOP8)

VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

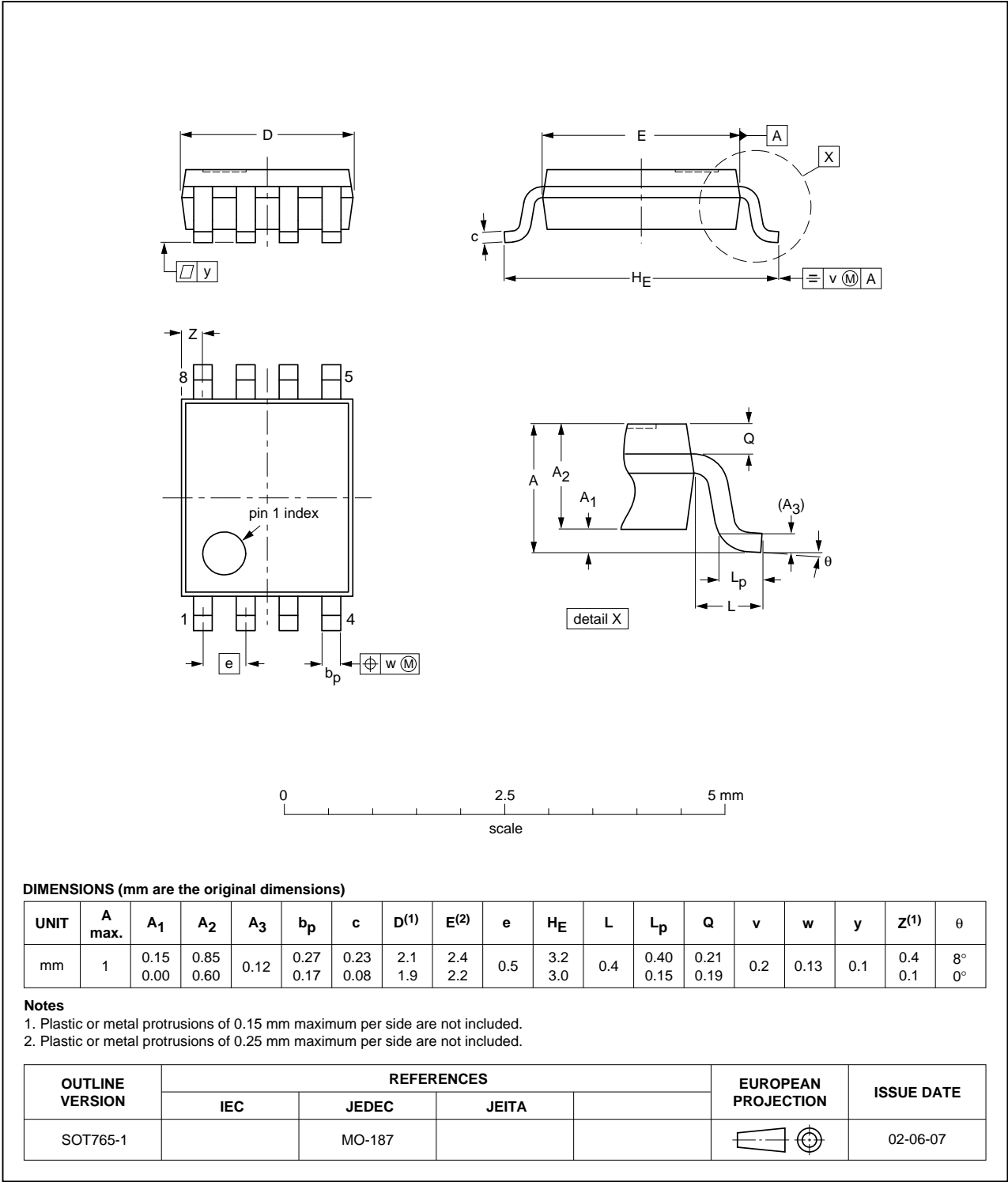


Fig 8. Package outline SOT765-1 (VSSOP8)

14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
MIL	Military
TTL	Transistor-Transistor Logic

15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT3G07_Q100 v.2	20131211	Product data sheet	-	74HC_HCT3G07_Q100 v.1
Modifications:	• Features and benefits updated (errata).			
74HC_HCT3G07_Q100 v.1	20130917	Product data sheet	-	-

16. Legal information

16.1 Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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